

USSN 09/900,662

AMENDMENTS OF CLAIMS

- 110K to
Entel
Dull
4/20/05
1. (Currently amended) A data storage device comprising an array of nanotubes as electron sources; and a phase-change storage layer proximate tips of the electron sources.
 2. (Original) The device of claim 1, wherein the nanotubes are carbon-based.
 3. (Original) The device of claim 1, wherein the nanotubes are boron nitride-based.
 4. (Cancelled)
 5. (Original) The device of claim 1, wherein each nanotube electron source is elongated.
 6. (Original) The device of claim 5, wherein the nanotubes have an aspect ratio greater than 10:1.
 7. (Original) The device of claim 1, further comprising word and bit lines for addressing the nanotubes.
 8. (Original) The device of claim 1, further comprising a micromover for positioning the array.